SILICON UV-ENHANCED PHOTODIODE CHIPS
DEVICE NO. : PD-0120U

1. Scope :

This specification applies to PIN silicon uv-enhanced photodiode chips, Device No. PD-0120U.

2. Structure :

2-1. Planar type : pin diode.

2-2. Electrodes :

Top side (Anode) : Aluminum alloy .

Back side (Cathode) : Gold alloy.

3. Size :

3-1. Chip size : 117 mils × 117 mils (2.970 mm × 2.970 mm).

3-2. Chip thickness : 12 ± 1.5 mils (0.305± 0.038 mm).

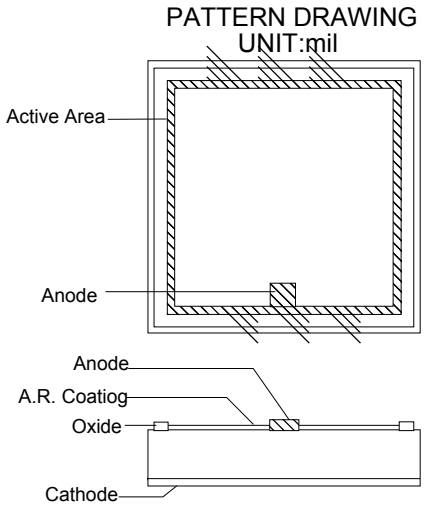
3-3. Active area : 97.2 mils × 97.2 mils (2.470 mm × 2.470 mm).

3-4. Bonding pad (anode) : 7.9 mils × 7.9 mils (0.200 mm × 0.200 mm).

3-5. Pattern drawing : refer to the attached drawing.

4. Electro-optical characteristics (Ta = 25℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse dark Current	I_D	V_R=10V H=0mw/cm²		5	30	nA
Reverse breakdown voltage	$V_{(BR)R}$	I_R=100uA H=0mw/cm²	33	120		V
Open circuit Voltage	Voc	C_T=2870° K H=5mw/cm²		350		mV
Short circuit current	Isc	C_T=2870° K H=5mw/cm²	40	55		uA
Reverse light Current	I_L	V_R =5V C_T=2870° K H=5mw/Cm²	40	60		uA
Total Capacitance	C_t	VR=0v		135	165	pF
		VR=1v		105	125	pF
		VR=2v		90	105	pF
		VR=3v		75	85	pF
		VR=4v		30	35	pF
		VR=5v		20	25	pF
Turn-on/ turn-off Time	ton/toff	V_R=10V R_L=1000Ω		50/50		nS
Sensitivty Wavelength Range	λ		190		1100	nm
peak sensitivity wavelength	λp			950		nm



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